

L Number	Hits	Search Text	DB	Time stamp
1	31025	semiconductor and ((thin adj film adj transistor) or tft)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:39
2	11501	(semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:40
3	7059	((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:40
4	2600	((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:41
5	1241	(((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:42
6	1235	(((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:42
7	733	((((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)) and substrate) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:43
8	573	((((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)) and substrate) and crystalliz\$5) and irradiat\$3 and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:43
9	544	((((((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)) and substrate) and crystalliz\$5) and irradiat\$3 and laser) and gate and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:44
10	461	(((((((((semiconductor and ((thin adj film adj transistor) or tft)) and (amorphous adj (silicon or si))) and plurality) and island) and (space or cavity or recess\$2 or groove or trench\$2)) and substrate) and crystalliz\$5) and irradiat\$3 and laser) and gate and source and drain and channel) and (polysilicon or (polycrystal\$4 adj (silicon or si)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/07 10:47